

Title (en)

Process for forming a layer of oxydes of aluminium and titanium on glass, obtained glass with a semiconducting layer.

Title (de)

Verfahren zur Bildung einer Schicht aus Aluminium- Titanoxiden auf Glas, das so erhaltene Glas mit halbleitenden Beschichtungen.

Title (fr)

Procédé de formation d'une couche d'oxydes d'aluminium et de titane sur du verre, vitrage comprenant le verre obtenu et une couche semi-conductrice.

Publication

EP 0465309 B1 19951115 (FR)

Application

EP 91401746 A 19910627

Priority

- FR 9008530 A 19900705
- FR 9008531 A 19900705

Abstract (en)

[origin: EP0677493A2] An aluminium-tin oxide layer is formed on glass by thermal decomposition of organic aluminium and tin cpds. in contact with the hot glass at below its softening temp., and oxidn. to form the layer. In the process, a soln. of a non-hydrolysable aluminium chelate and one or more organic tin cpds. is sprayed on to the hot glass. Also claimed are: (i) a product obtained by the above process and comprising a glass support with an aluminium-tin oxide layer having a refractive index of 1.65-1.76; and (ii) low emissivity glazing, heating glazing (pref. in laminated form with an interposed foil of PVB, PVC or PU), glazing for use as substrate for opto-electronic devices and anti-reflection glazing, the glazing including the above product. The aluminium chelate is pref. aluminium acetylacetonate or aluminium isovaleryl acetonate. The tin cpd. is pref. dibutyltin oxide (DBTO) or dibutyltin acetate (DBTA). The soln. pref. contains 13-30 vol.% DBTA or 30-50 vol.% DBTO and has an Al/Sn wt. ratio of 0.10-0.70. The glass is pref. at 600-650 degrees C and is pref. moved at 3-25 m./sec.

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C03C 17/25; **C03C 17/34**

IPC 8 full level

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CPC (source: EP)

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Cited by

WO2004026782A1; CN1323045C; DE102008005283B4; DE102008005283A1; EP0573325A1; US5635287A; EP1514852A1; US7550208B2; WO2004067791A3; US7713638B2; FR2702208A1; GB2275692A; GB2275692B; BE1008565A4; ES2097079A1; US5730771A; AT405280B; FR2701474A1

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